TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2244FK

Low-Voltage Octal Bus Buffer with 3.6 V Tolerant Inputs and Outputs

The TC7MA2244FK is a high performance CMOS octal bus buffer. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This device is non-inverting 3-state buffer having four active-low output enables. When the \overline{ST} input is high, the outputs are in a high impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The 26 Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

Features

- 26 Ω series resistors on outputs.
- Low voltage operation: V_{CC} = 1.8~3.6 V
- High speed operation: $t_{pd} = 4.4 \text{ ns} (\text{max}) (V_{CC} = 3.0 \sim 3.6 \text{ V})$

$$t_{pd} = 5.6 \text{ ns} (\text{max}) (\text{V}_{CC} = 2.3 \sim 2.7 \text{ V})$$

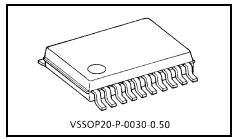
$$t_{pd} = 9.8 \text{ ns} (\text{max}) (\text{V}_{CC} = 1.8 \text{ V})$$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA} (min) (V_{CC} = 3.0 \text{ V})$

$$I_{OH}/I_{OL} = \pm 8 \text{ mA} \text{ (min)} (V_{CC} = 2.3 \text{ V})$$

$$I_{OH}/I_{OL} = \pm 4 \text{ mA} \text{ (min)} (V_{CC} = 1.8 \text{ V})$$

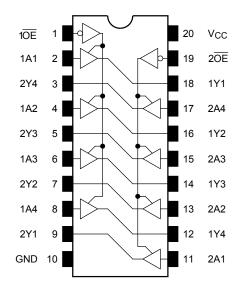
- Latch-up performance: -300 mA
- ESD performance: Machine model $\ge \pm 200 \text{ V}$ Human body model $\ge \pm 2000 \text{ V}$
- Package: VSSOP (US)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.



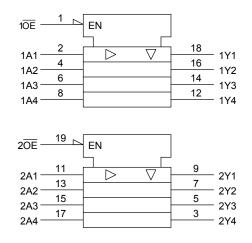
Weight: 0.03 g (typ.)

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Pin Assignment (top view)



IEC Logic Level



Truth Table

Inp	Outputs		
OE	A _n	Outputs	
L	L	L	
L	Н	Н	
Н	Х	Z	

X: Don't care

Z: High impedance

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	VIN	-0.5~4.6	V	
DC output voltage	Vour	-0.5~4.6 (Note 2)	V	
DC output voltage	Vout	-0.5~V _{CC} + 0.5 (Note 3)	v	
Input diode current	I _{IK}	-50	mA	
Output diode current	Іок	±50 (Note 4)	mA	
DC output current	lout	±50	mA	
Power dissipation	PD	180	mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Off-state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.8~3.6	V
Supply vollage	vcc	1.2~3.6 (Note 2)	v
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	Vout	0~3.6 (Note 3)	V
Output voltage	V001	0~V _{CC} (Note 4)	v
		±12 (Note 5)	
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA
		±4 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: Off-state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{~} 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 V$

Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = $-40 \sim 85^{\circ}$ C, 2.7 V < V_{CC} \leq 3.6 V)

Character	stics	Symbol	Tes	Test Condition		Min	Max	Unit	
Input voltage	High level	VIH		_	2.7~3.6	2.0	—	V	
Input voltage	Low level	VIL		_	2.7~3.6	_	0.8	v	
				I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	_		
	High level	Vон	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -6 \text{ mA}$	2.7	2.2	_		
	-			$I_{OH} = -8 \text{ mA}$	3.0	2.4	_		
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2	_	V	
		V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100 \ \mu A$	2.7~3.6	_	0.2		
	Low level			$I_{OL} = 6 \text{ mA}$	2.7	_	0.4		
	LOW IEVEI			$I_{OL} = 8 \text{ mA}$	3.0	_	0.55		
				$I_{OL} = 12 \text{ mA}$	3.0	_	0.8		
Input leakage curre	nt	lin	V _{IN} = 0~3.6 V		2.7~3.6		±5.0	μA	
3-state output off-st	tate current	loz	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$		_	±10.0	μA	
3-state output off-state current		102	V _{OUT} = 0~3.6 V		2.7~3.6		±10.0	μΛ	
Power off leakage of	current	IOFF	$V_{IN}, V_{OUT} = 0 \sim 3.6 V$		0	—	10.0	μA	
		laa	$V_{IN} = V_{CC}$ or GND		2.7~3.6	—	20.0		
Quiescent supply c	urrent	Icc	$V_{CC} \leqq (V_{IN}, V_{OUT}) \leqq$	3.6 V	2.7~3.6	_	±20.0	μA	
			$V_{IH} = V_{CC} - 0.6 V$ (pe	er input)	2.7~3.6	_	750		

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Character	istics	Symbol	Tes	Test Condition		Test Condition		Test Condition		Min	Max	Unit
Input voltage	High level	VIH		_	2.3~2.7	1.6	_	V				
Input voltage	Low level	VIL		_	2.3~2.7		0.7	v				
				$I_{OH} = -100 \ \mu A$	2.3~2.7	V _{CC} - 0.2	_					
	High level	VOH	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -4 \text{ mA}$	2.3	2.0	_					
Output voltage	0.1		$I_{OH} = -6 \text{ mA}$	2.3	1.8	_						
				$I_{OH} = -8 \text{ mA}$	2.3	1.7	_	V				
			$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 100 μA	2.3~2.7	_	0.2					
	Low level	V _{OL}		$I_{OL} = 6 \text{ mA}$	2.3	_	0.4					
				I _{OL} = 8 mA	2.3	_	0.6					
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μA				
2 state output off c	tata aurrant	1	$V_{IN} = V_{IH} \text{ or } V_{IL}$		2.3~2.7		±10.0					
3-state output off-state current		I _{OZ}	V _{OUT} = 0~3.6 V		2.3~2.1	_	±10.0	μA				
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μA				
			$V_{IN} = V_{CC} \text{ or } GND$	V _{IN} = V _{CC} or GND		_	20.0					
Quiescent supply of	Juneni	Icc	$V_{CC} \stackrel{\scriptstyle \leq}{=} (V_{IN},V_{OUT}) \stackrel{\scriptstyle \leq}{=}$	3.6 V	2.3~2.7	_	±20.0	μA				

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	VIH			1.8~2.3	$0.7 \times V_{CC}$	_	V
input voltage	Low level	VIL			1.8~2.3	_	$0.2 \times V_{CC}$	v
	High level	Vон	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage	Ū	0.1		$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	V
Low level	Vai	VIN = VIH or VIL	I _{OL} = 100 μA	1.8	_	0.2		
	LOWIEVEI	V _{OL}	VIN = VIH OI VIL	$I_{OL} = 4 \text{ mA}$	1.8		0.3	
Input leakage curren	nt	l _{IN}	V _{IN} = 0~3.6 V		1.8		±5.0	μA
3-state output off-sta	3-state output off-state current I_{OZ} $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0~3.6 \text{ V}$		1.8		±10.0	μA		
Power off leakage c	urrent	I _{OFF}	$V_{IN}, V_{OUT} = 0 \sim 3.6 V$		0		10.0	μA
Quiescent supply o	urrent	Icc	$V_{IN} = V_{CC} \text{ or } GND$	IN = V _{CC} or GND			20.0	μA
Quiescent supply ct	Quiescent supply current		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8		±20.0	μΛ

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition		Min	Max	Unit
	Cymbol		$V_{CC}(V)$		max	Onic
	+		1.8	1.5	9.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	5.6	ns
	^t pHL		$\textbf{3.3}\pm\textbf{0.3}$	0.6	4.4	
3-state output enable		Figure 1, Figure 3	1.8	1.5	9.8	
	^t pZL tpZH		2.5 ± 0.2	0.8	6.5	ns
			$\textbf{3.3}\pm\textbf{0.3}$	0.6	5.0	
		Figure 1, Figure 3	1.8	1.5	7.2	
3-state output disable	t _{pLZ}		2.5 ± 0.2	0.8	3.9	ns
	^t pHZ		$\textbf{3.3}\pm\textbf{0.3}$	0.6	3.6	
Output to output skew		(Note)	1.8	_	0.5	
	t _{osLH}		2.5 ± 0.2	_	0.5	ns
	t _{osHL}		$\textbf{3.3}\pm\textbf{0.3}$	_	0.5	

For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics (Ta = 25° C, Input: t_r = t_f = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition			Tun	Unit
Characteristics	Symbol	Test Condition		$V_{CC}\left(V\right)$	Тур.	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	0.15	
Quiet output maximum dynamic V_{OL}	VOLP	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	-0.15	
Quiet output minimum dynamic V_{OL}	V _{OLV}	$V_{IH} = 2.5 V, V_{IL} = 0 V$ (N	ote)	2.5	-0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	1.55	
Quiet output minimum dynamic V_{OH}	VOHV	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	2.65	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol Test Condition			Tun	Unit	
Characteristics	Symbol			V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO			1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	CPD	$f_{IN} = 10 \text{ MHz}$ (N	lote)	1.8, 2.5, 3.3	20	pF

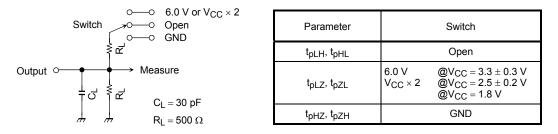
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$

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AC Test Circuit





AC Waveform

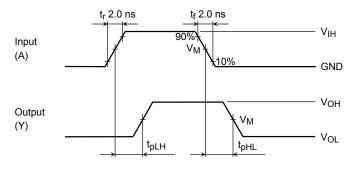


Figure 2 t_{pLH}, t_{pHL}

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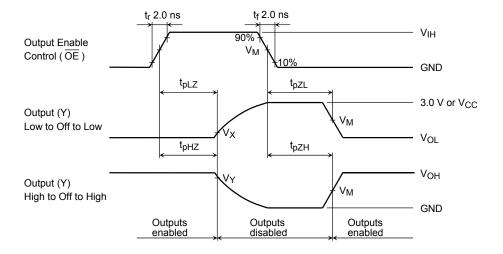
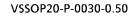


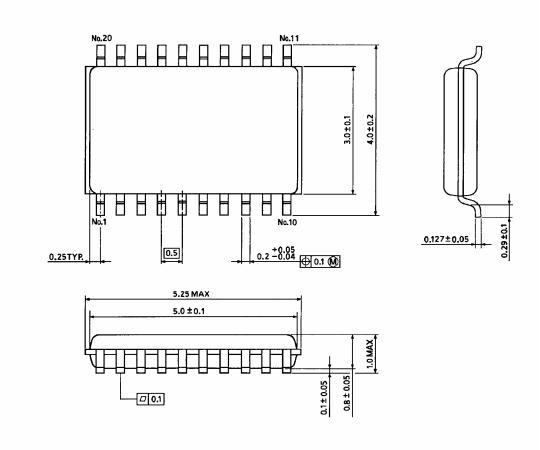
Figure 3	t _{pLZ} , t _{pH}	IZ, tpZL, tpZH	
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Symbol	V _{CC}						
Symbol	$3.3\pm0.3~V$	$2.5\pm0.2~\text{V}$	1.8 V				
VIH	2.7 V	V _{CC}	V _{CC}				
VM	1.5 V	V _{CC} /2	V _{CC} /2				
Vx	V_{OL} + 0.3 V	V _{OL} + 0.15 V	V_{OL} + 0.15 V				
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V				

Package Dimensions



Unit : mm



Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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